

Dimitrios Velessiotis

List of Publications by Year in descending order

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18
papers

248
citations

1163117

8
h-index

996975

15
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18
all docs

18
docs citations

18
times ranked

350
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Vertical devices of self-assembled hybrid organic/inorganic monolayers based on tungsten polyoxometalates. <i>Microelectronic Engineering</i> , 2008, 85, 1399-1402. | 2.4 | 54 |
| 2 | Tunneling transport in polyoxometalate based composite materials. <i>Applied Physics Letters</i> , 2003, 83, 488-490. | 3.3 | 47 |
| 3 | Molecular Storage Elements for Proton Memory Devices. <i>Advanced Materials</i> , 2008, 20, 4568-4574. | 21.0 | 36 |
| 4 | Development mechanism study by dissolution monitoring of positive methacrylate photoresists. <i>Microelectronic Engineering</i> , 2000, 53, 489-492. | 2.4 | 25 |
| 5 | Tungstate polyoxometalates as active components of molecular devices. <i>Journal of Applied Physics</i> , 2005, 98, 084503. | 2.5 | 22 |
| 6 | Molecular junctions made of tungsten-polyoxometalate self-assembled monolayers: Towards polyoxometalate-based molecular electronics devices. <i>Microelectronic Engineering</i> , 2011, 88, 2775-2777. | 2.4 | 17 |
| 7 | Aqueous base development and acid diffusion length optimization in negative epoxy resist for electron beam lithography. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 3431. | 1.6 | 9 |
| 8 | Transport properties of polyoxometalate containing polymeric materials. <i>Synthetic Metals</i> , 2003, 138, 267-269. | 3.9 | 8 |
| 9 | Hybrid organic-inorganic materials for molecular proton memory devices. <i>Organic Electronics</i> , 2009, 10, 711-718. | 2.6 | 8 |
| 10 | Emergence of ambient temperature ferroelectricity in <i>meso</i> -tetrakis(1-methylpyridinium-4-yl)porphyrin chloride thin films. <i>Applied Physics Letters</i> , 2013, 103, 022908. | 3.3 | 5 |
| 11 | Phosphorous Diffusion in N ₂ ⁺ -Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P418-P428. | 1.8 | 5 |
| 12 | Application of the partial wave expansion method in 3-D low energy electron beam lithography simulation. <i>Microelectronic Engineering</i> , 2001, 57-58, 297-302. | 2.4 | 4 |
| 13 | (Invited) Issues with n-type Dopants in Germanium. <i>ECS Transactions</i> , 2018, 86, 51-58. | 0.5 | 4 |
| 14 | Molecular nanodevices based on functionalized cyclodextrins. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 2532-2535. | 1.8 | 2 |
| 15 | Conduction mechanisms in tungsten-polyoxometalate self-assembled molecular junctions. <i>Microelectronic Engineering</i> , 2012, 97, 150-153. | 2.4 | 2 |
| 16 | Compound polymeric materials in molecular nanodevices: electrical behavior of zero-dimension semiconducting inorganic molecules embedded in a polymer substrate. <i>Journal of Physics: Conference Series</i> , 2005, 10, 93-96. | 0.4 | 0 |
| 17 | Substrate damage in ion-implanted (100) germanium after extended ms flash lamp annealing: Origins and suppression. <i>Materials Science in Semiconductor Processing</i> , 2021, 122, 105477. | 4.0 | 0 |
| 18 | Post-metallization annealing and photolithography effects in p-type Ge/Al ₂ O ₃ /Al MOS structures. <i>ECS Journal of Solid State Science and Technology</i> , 0, , . | 1.8 | 0 |